

Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from, Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

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2SC4808J

Silicon NPN epitaxial planar type

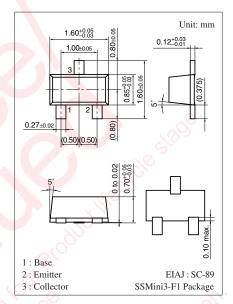
For UHF band low-noise amplification

■ Features

- Low noise figure NF
- High forward transfer gain $|S_{21e}|^2$
- High transition frequency f_T
- SS-Mini type package, allowing downsizing of the equipment and automatic insertion through the tape packing.

■ Absolute Maximum Ratings $T_a = 25^{\circ}C$

| Parameter | Symbol | Rating | Unit | |
|---------------------------------------|------------------|-------------|------|--|
| Collector-base voltage (Emitter open) | V_{CBO} | 15 | V | |
| Collector-emitter voltage (Base open) | V_{CEO} | 10 | V | |
| Emitter-base voltage (Collector open) | V _{EBO} | 2 | V | |
| Collector current | I_{C} | 80 | mA | |
| Collector power dissipation | P_{C} | 125 | mW | |
| Junction temperature | T _j | 125 | °C | |
| Storage temperature | T _{stg} | -55 to +125 | °C | |



Marking Symbol: 3M

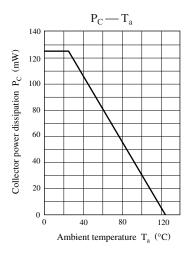
■ Electrical Characteristics $T_a = 25^{\circ}C \pm 3^{\circ}C$

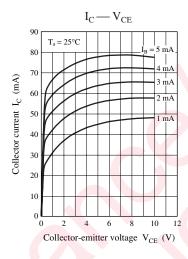
| Parameter | Symbol | Conditions | Min | Тур | Max | Unit |
|---|----------------------|--|-----|-----|-----|------|
| Collector-base voltage (Emitter open) | V _{CBO} | $I_{\rm C} = 10 \ \mu A, I_{\rm E} = 0$ | 15 | | | V |
| Collector-emitter voltage (Base open) | V _{CEO} | $I_{\rm C} = 100 \ \mu A, I_{\rm B} = 0$ | 10 | | | V |
| Collector-base cutoff current (Emitter open) | I_{CBO} | $V_{CB} = 10 \text{ V}, I_E = 0$ | 1.9 | | 1 | μΑ |
| Emitter-base cutoff current (Collector open) | I_{EBO} | $V_{EB} = 2 V, I_C = 0$ | | | 1 | μΑ |
| Forward current transfer ratio * | h _{FE} | $V_{CE} = 8 \text{ V}, I_{C} = 20 \text{ mA}$ | 50 | 150 | 300 | _ |
| Transition frequency | f_T | $V_{CE} = 8 \text{ V}, I_{C} = 15 \text{ mA}, f = 0.8 \text{ GHz}$ | 5 | 6 | | GHz |
| Collector output capacitance (Common base, input open circuited) | C _{ob} | $V_{CB} = 10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$ | | 0.7 | 1.2 | pF |
| Forward transfer gain | S _{21e} 2 | $V_{CE} = 8 \text{ V}, I_{C} = 15 \text{ mA}, f = 0.8 \text{ GHz}$ | 11 | 14 | | dB |
| Maximum unilateral power gain | G_{UM} | $V_{CE} = 8 \text{ V}, I_{C} = 15 \text{ mA}, f = 0.8 \text{ GHz}$ | | 15 | | dB |
| Noise figure | NF | $V_{CE} = 8 \text{ V}, I_{C} = 7 \text{ mA}, f = 0.8 \text{ GHz}$ | | 1.3 | 2.0 | dB |

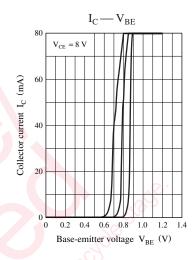
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

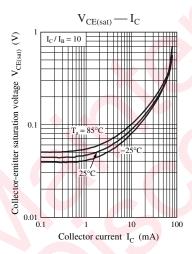
2. *: Pulse measurement

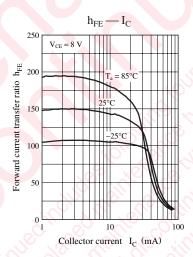
Panasonic

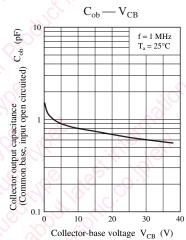












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